

N-channel TrenchMOS standard level FET

Rev. 03 — 16 December 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance

1.3 Applications

- DC-to-DC converters
- General purpose switching
- Motor control circuits

- Suitable for high frequency applications due to fast switching characteristics
- Off-line switched-mode power supplies
- TV and computer monitor power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	200	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}$	-	-	8.7	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	-	88	W
Static cha	aracteristics					
R_{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 4.5 A; T _j = 25 °C	-	300	400	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 9 A; V _{DS} = 160 V; T _i = 25 °C	-	12	-	nC

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number Package			
	Name	Description	Version
PHD9NQ20T	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

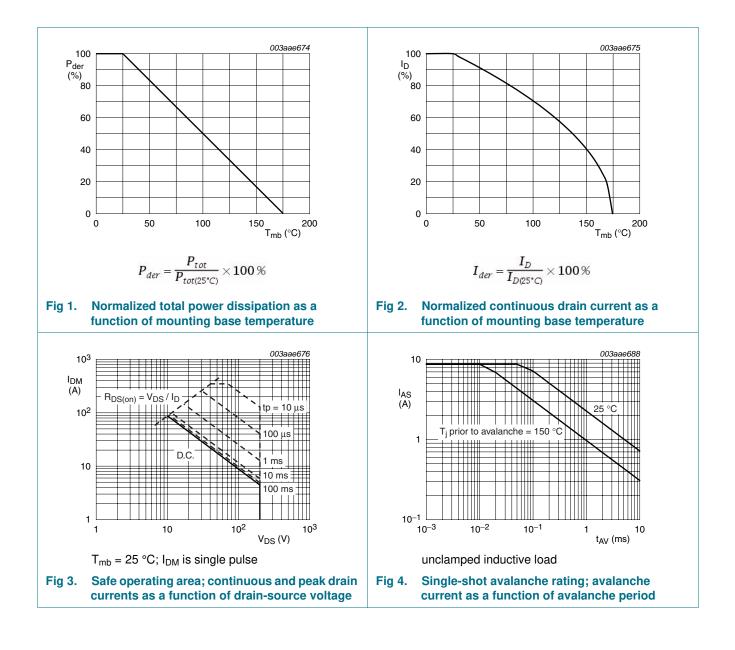
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	200	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	200	V
V _{GS}	gate-source voltage		-30	30	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C	-	6.2	А
		V _{GS} = 10 V; T _{mb} = 25 °C	-	8.7	А
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	35	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	88	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature	junction temperature		175	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	8.7	А
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	35	А
Avalanche r	ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{\text{D}} = 7.2 \text{ A}; \\ V_{sup} \leq 25 \text{ V}; \text{ unclamped}; \text{t}_{p} = 100 \mu\text{s}; \\ R_{GS} = 50 \Omega $	-	93	mJ
I _{AS}	non-repetitive avalanche current	$\label{eq:V_sup} \begin{array}{l} V_{sup} \leq 25 \ V; \ V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ ^{\circ}C; \\ R_{GS} = 50 \ \Omega; \ unclamped \end{array}$	-	8.7	А
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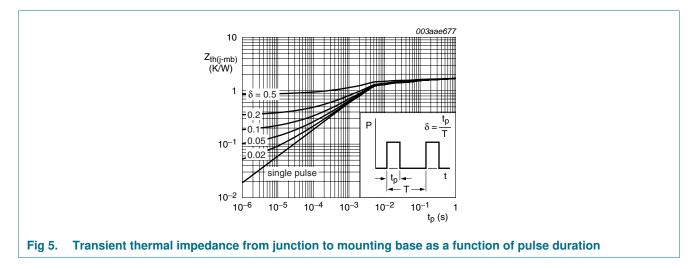
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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	1.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board; minimum footprint	-	50	-	K/W



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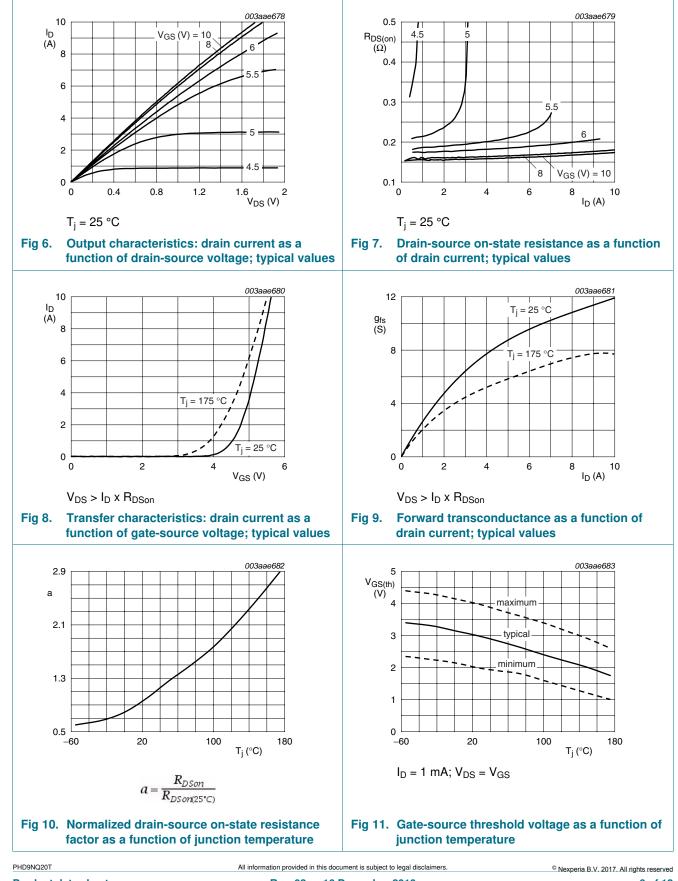
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	200	-	-	V
	voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	178	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
I _{DSS}	drain leakage current	$V_{DS} = 200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		V_{DS} = 200 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 4.5 A; T _j = 175 °C	-	-	1.16	Ω
	resistance	V_{GS} = 10 V; I _D = 4.5 A; T _j = 25 °C	-	300	400	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 9 \text{ A}; V_{DS} = 160 \text{ V}; V_{GS} = 10 \text{ V};$	-	24	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	4	-	nC
Q _{GD}	gate-drain charge		-	12	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	959	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	93	-	pF
C _{rss}	reverse transfer capacitance		-	54	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 100 V; R_L = 10 Ω; V_{GS} = 10 V;	-	8	-	ns
t _r	rise time	R _{G(ext)} = 5.6 Ω; T _j = 25 °C	-	19	-	ns
t _{d(off)}	turn-off delay time		-	25	-	ns
t _f	fall time		-	15	-	ns
9 _{fs}	transfer conductance	$V_{DS} = 25 \text{ V}; I_D = 4.5 \text{ A}; T_j = 25 \text{ °C}$	3.8	6	-	S
L _D	internal drain inductance	from tab to centre of die ; $T_j = 25 \text{ °C}$	-	3.5	-	nH
L _S	internal source inductance	From source lead to source bond pad ; $T_j = 25 \ ^\circ C$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = 9 A; V _{GS} = 0 V; T _j = 25 °C	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 9 A; dI _S /dt = -100 A/μs;	-	92	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	0.5	-	μC

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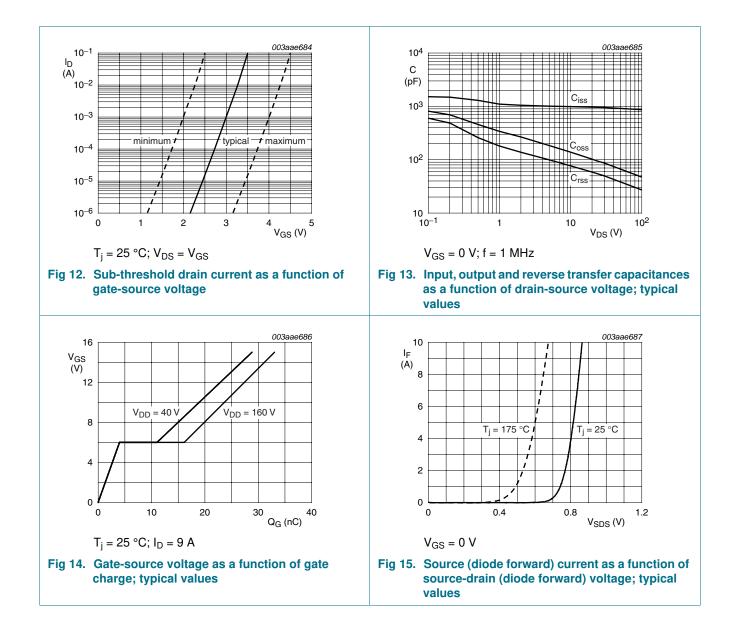
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7. Package outline

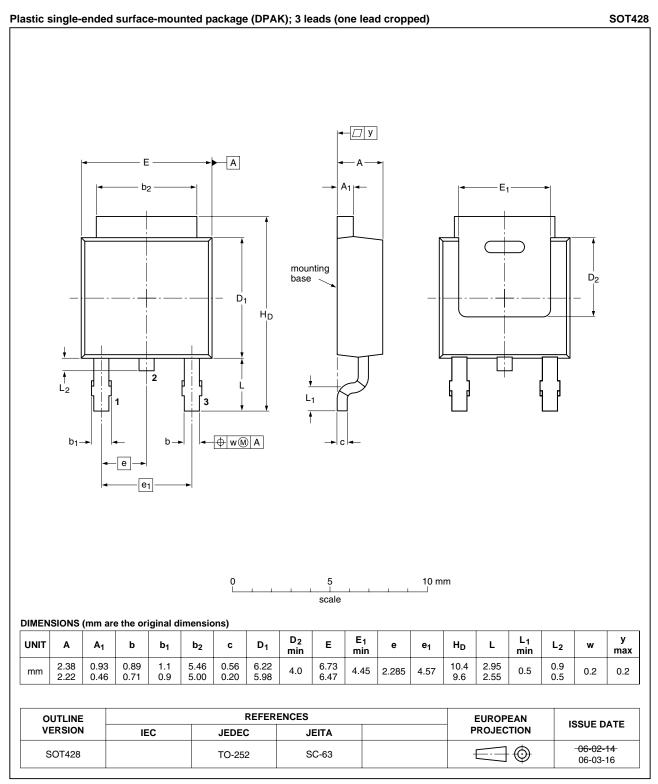


Fig 16. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHD9NQ20T v.3	20101216	Product data sheet	-	PHB_PHD_PHP9NQ20T v.2
Modifications:		of this data sheet has bee f NXP Semiconductors.	en redesigned to co	mply with the new identity
	 Legal texts I 	have been adapted to the	new company nam	ne where appropriate.
	 Type number 	er PHD9NQ20T separated	d from data sheet P	HB_PHD_PHP9NQ20T v.2.
PHB_PHD_PHP9NQ20T v.2	20001001	Product specification	-	PHB_PHD_PHP9NQ20T v.1

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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